

# **Dual P-Channel 30-V (D-S) MOSFET**

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)		
- 30	0.036 at V <sub>GS</sub> = - 10 V	- 5.2		
	0.055 at V <sub>GS</sub> = - 4.5 V	- 4.2		

### **FEATURES**

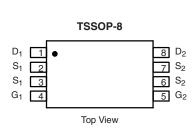
- Halogen-free
- TrenchFET® Power MOSFETs

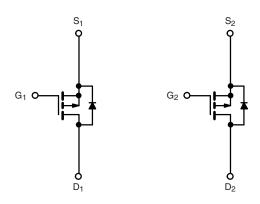


ROHS

### **APPLICATIONS**

- · Load Switch
- · Battery Switch





P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T	$_{A}$ = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 30		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Continuous Drain Current /T 150 °C\a	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 5.2	- 4.1	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		- 4.2	- 3.6	Δ.
Pulsed Drain Current (10 µs Pulse Width)		I <sub>DM</sub>	- 30		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 1.0	- 0.70	
Manianum Danier Disabation d	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.14	0.83	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		0.73	0.53	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum landing to Audienta	t ≤ 10 s	- R <sub>thJA</sub>	86	110	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		124	150	°C/W
Maximum Junction-to-Foot	Steady State	R <sub>thJF</sub>	52	65	

#### Notes:

a. Surface Mounted on 1" x 1" FR4 board.



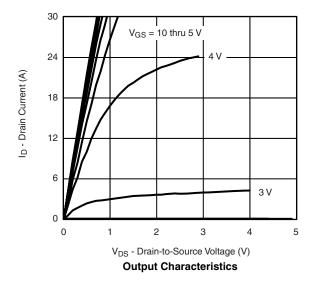
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	•						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	_	V <sub>DS</sub> = - 30 V, V <sub>GS</sub> = 0 V			- 1		
	I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			- 10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 15			Α	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 4.7 A		0.036		-	
		$V_{GS} = -4.5 \text{ V}, I_D = -3.8 \text{ A}$		0.055		Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 4.7 A		14		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 1.0 A, V <sub>GS</sub> = 0 V		- 0.74	- 1.1	V	
Dynamic <sup>b</sup>				1			
Total Gate Charge	Qg			13	20		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.7 \text{ A}$		3		nC	
Gate-Drain Charge	$Q_{gd}$			5.8		1	
Gate Resistance	$R_{g}$	f = 1.0 MHz		4.6		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			13	20		
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 15 $\Omega$		14	22		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 1 A, $V_{GEN}$ = - 10 V, $R_G$ = 6 $\Omega$		52	80	ns	
Fall Time	t <sub>f</sub>			26	40		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 1.0 A, dl/dt = 100 A/μs		40	60		

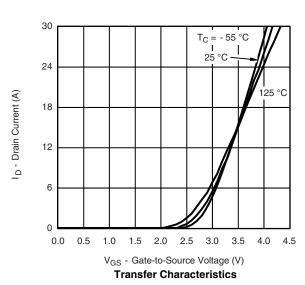
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

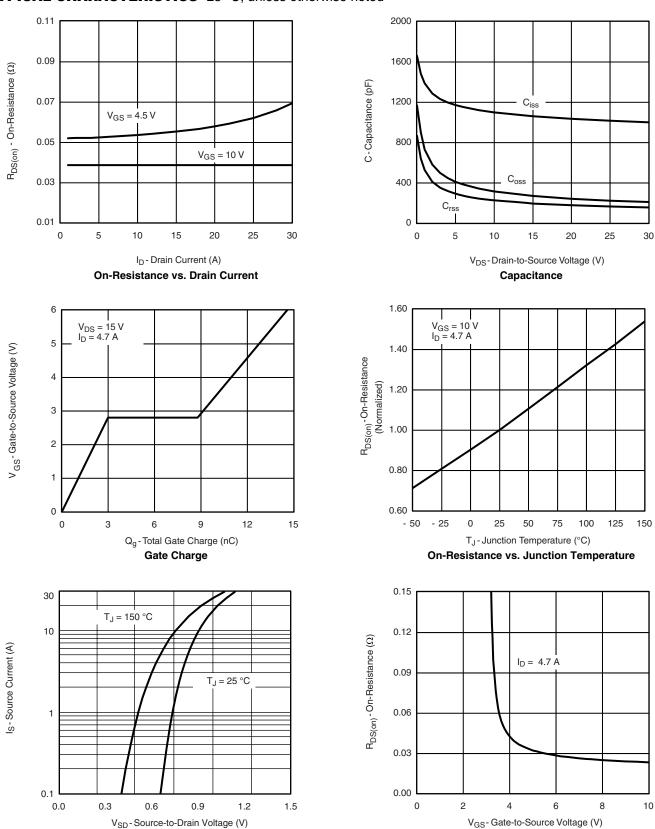
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







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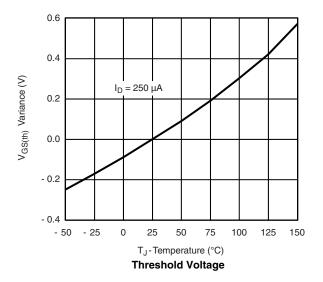
E-mail: China@VBsemi TEL:86-755-83251052

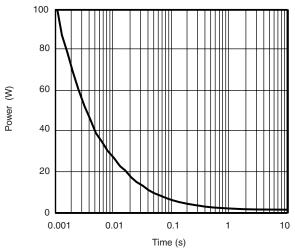
Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

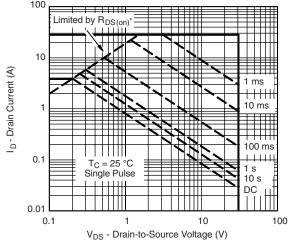


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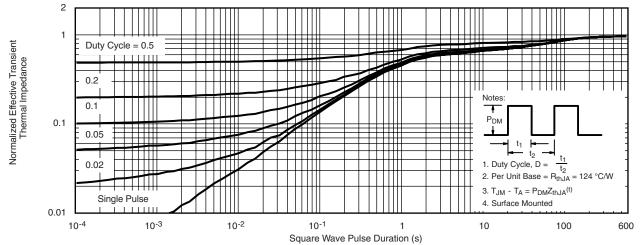




Single Pulse Power, Junction-to-Ambient



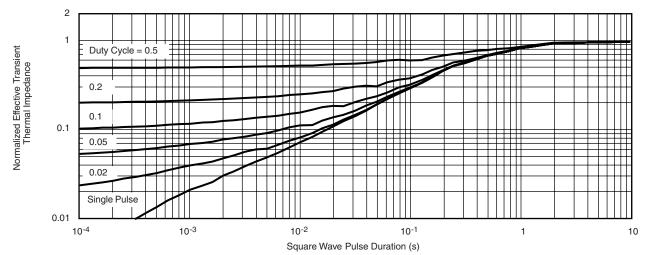
\* V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified **Safe Operating Area, Junction-to-Case** 



Normalized Thermal Transient Impedance, Junction-to-Ambient



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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